

REMARKS

This is intended as a full and complete response to the Office Action dated June 3, 2005, having a shortened statutory period for response set to expire on September 3, 2005. Claims 1-20 remain pending in the application and are shown above. Claim 20 is rejected and claims 1-19 are indicated to be allowable by the Examiner. Reconsideration of the rejected claims is requested for reasons presented below.

Claim 20 is rejected under 35 U.S.C. § 102(e) as being anticipated by *Xu et al.* (U.S. Patent No. 6,656,837). The Examiner asserts that *Xu et al.* discloses the subject matter as recited in claim 20. Applicant respectfully responds to the rejection.

Xu et al. discloses depositing a silicon oxycarbide layer on a silicon carbide layer, with the silicon oxycarbide layer is formed from a plasma of an oxidizing gas and an organosilicon compound. The deposited silicon carbide layer may be treated by a plasma of an inert gas.

Xu et al. does not suggest or motivate forming an initiation layer on a barrier layer by introducing an oxidizing gas into the processing chamber and generating a plasma of the oxidizing gas prior to introducing an organosilicon compound into the processing chamber.

Xu et al. does not teach, show or suggest positioning the substrate in a processing chamber, wherein the substrate has a barrier layer comprising at least silicon and carbon, introducing an oxidizing gas into the processing chamber, generating a plasma of the oxidizing gas, forming an initiation layer on the barrier layer by exposing the barrier layer to the plasma of the oxidizing gas, introducing an organosilicon compound into the processing chamber after forming the initiation layer, reacting the organosilicon compound and the oxidizing gas, and depositing a first dielectric layer adjacent the initiation layer, wherein the dielectric layer comprises silicon, oxygen, and carbon and has a dielectric constant of about 3 or less, as recited in claim 20. Withdrawal of the rejection is respectfully requested.

In conclusion, the references cited by the Examiner, alone or in combination, do not teach, show, or suggest the invention as claimed.

The secondary references made of record are noted. However, it is believed that the secondary references are no more pertinent to the Applicant's disclosure than the primary references cited in the office action. Therefore, Applicant believes that a detailed discussion of the secondary references is not necessary for a full and complete response to this office action.

Having addressed all issues set out in the office action, Applicant respectfully submits that the claims are in condition for allowance and respectfully request that the claims be allowed.

Respectfully submitted,



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